



1Gb to 64Gb configuration solutions to boot the last generation of FPGAs

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October, 4th, 2023



AGENDA

1. COMBO (COntfiguration Memory Boot Manager)

Up to 64Gb loader / scrubber to boot SRAM based FPGAs

2. MNEMOSYNE (1Gb Configuration Memory)

512Mb – 1Gb RHBD Non-volatile Memory

3. CONCLUSION





COMBO

(COnfiguration Memory
Boot Manager)



INTRODUCTION COMBO

Market Needs: Increase Need In Configuration Memory Density

- Newly released space SRAM FPGAs are requiring larger configuration memories.

AMD XILINX Space FPGAs	Configuration memory density
Virtex-4QV - XQR4V	64 Mb
Virtex-5QV - XQR5V	64 Mb
RT Kintex Ultrascale - XQRKU060	256 Mb
Zynq Ultrascale+	256 Mb
Versal -XQRV	≥ 1 Gb

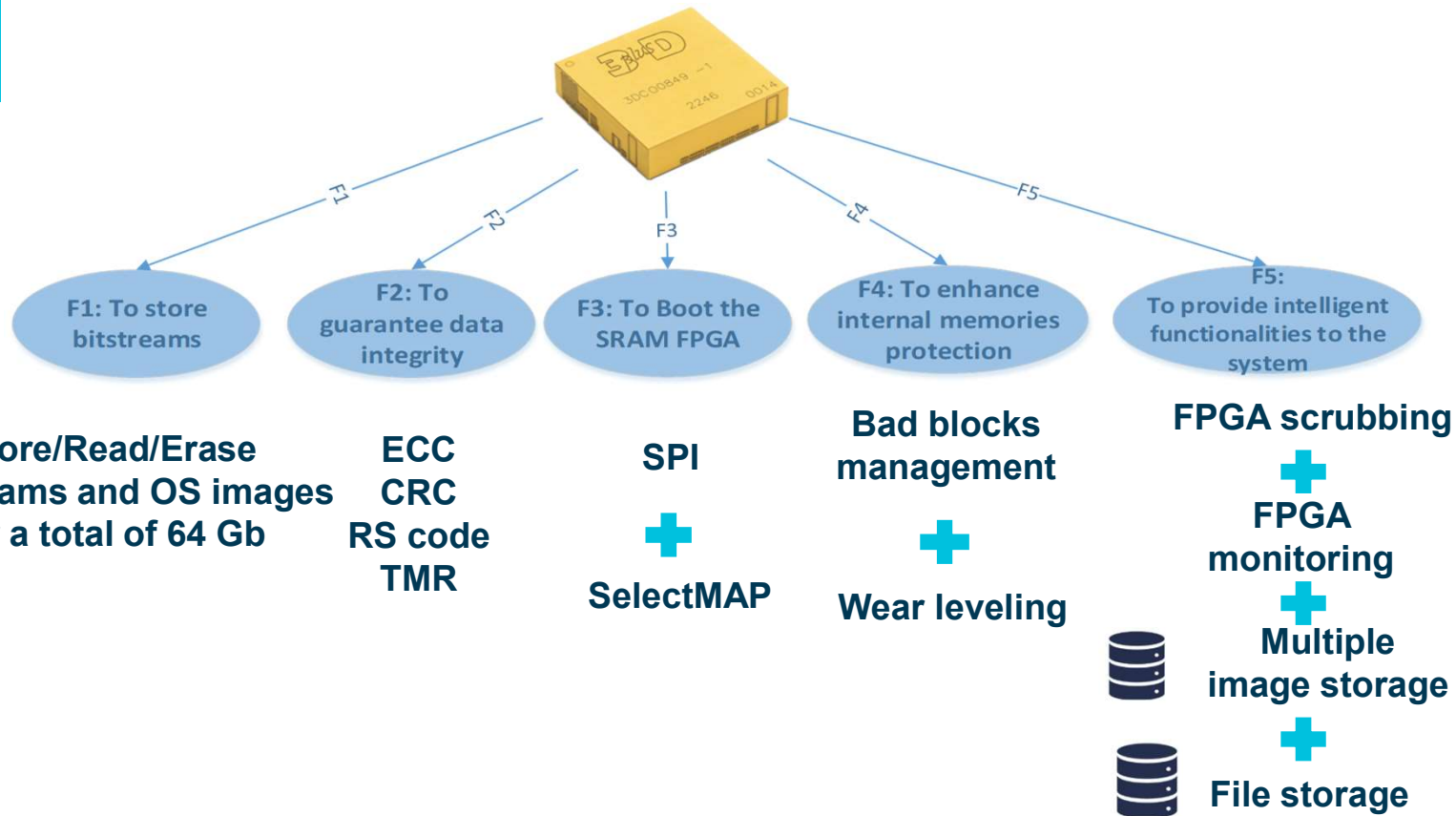
- Nowadays, space applications are requiring :
 - Multiple bitstream images
 - In-orbit reconfigurability
 - Improvement of the overall reliability by scrubbing the memories and FPGAs
- 3D-PLUS proposes a space grade high density **CO**nfiguration **M**emory **BO**ot manager **COMBO** family to boot and/or scrub SRAM based FPGAs/MPSoC requiring a smart integrated solution.





COMBO FUNCTIONALITIES

What Functionalities Does Combo Family Provide?

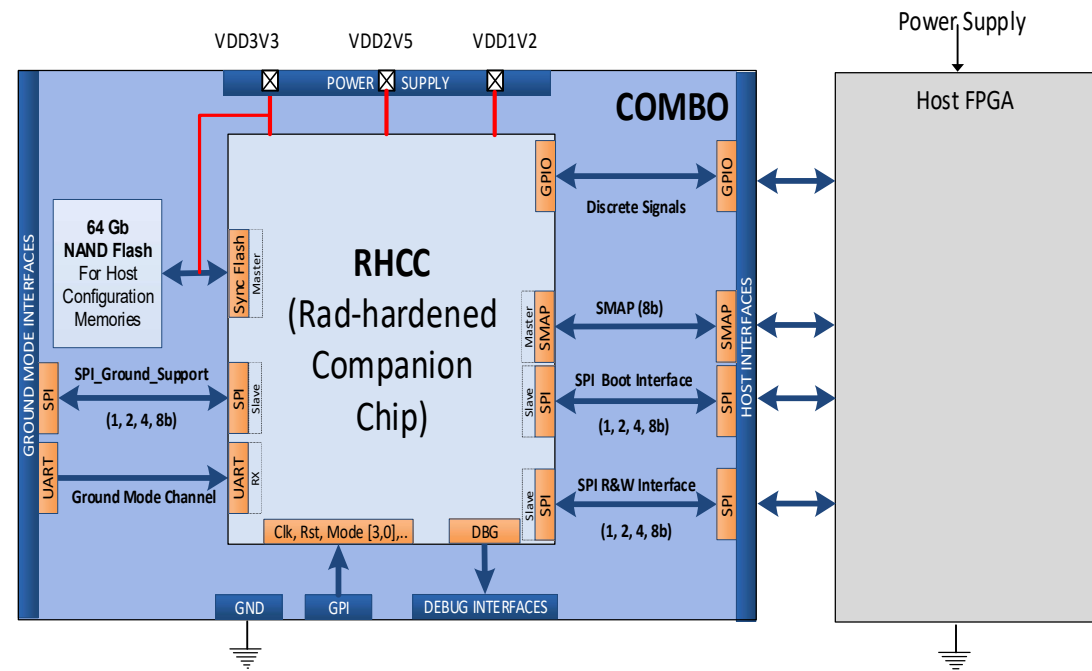




COMBO INTERFACES

What Are Combo Interfaces?

- On ground, the UART/SPI interface allows to:
 - Read/write/erase files
 - Store the Initial file system tables and missions parameters
- During the mission, the 2 SPI interfaces can be used to :
 - One to boot the SRAM based FPGA
 - One to perform read/write files
- During the mission, SelectMap interface can be used to :
 - Boot the SRAM-based FPGA
 - Detect errors on the configuration layer of the FPGA
 - Scrubs and monitors the SRAM based FPGA.





COMBO CHARACTERISTICS

Companion For Space Application

Test campaign already performed.

Radiation performances:

- TID > 50 kRad
- SEL LET > 62.5MeV.cm²/mg

Environment Performances:

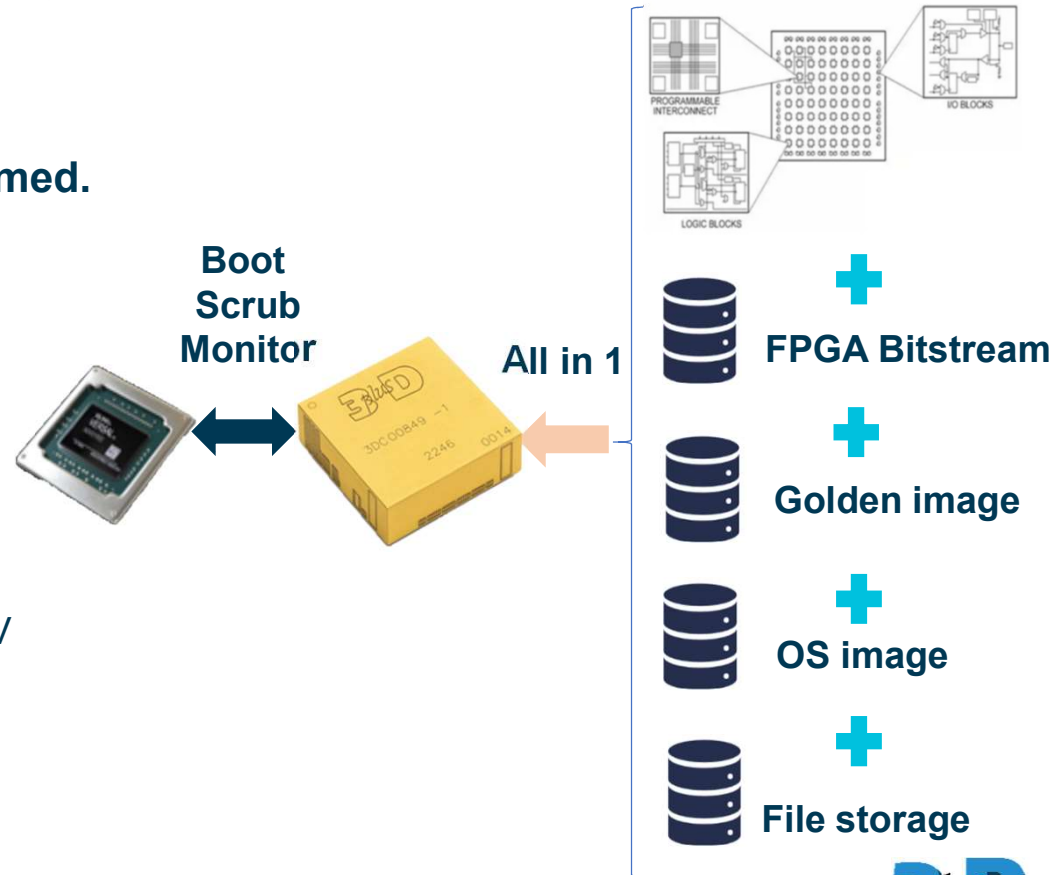
- 40°C to +105°C

Electrical power supply:

- Power Supply: 1.2V, 2.5V, 3.3V

Package

Product footprint : 32x32mm²
484-ball BGA, pitch: 1,27mm
Weight: 22g



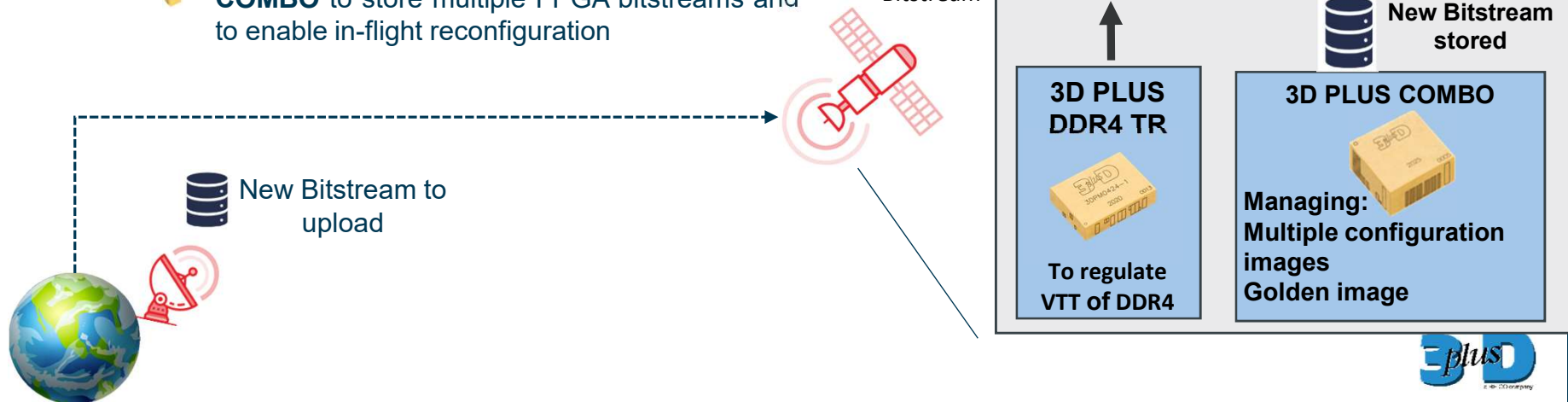


IN-FLIGHT RECONFIGURATION FOR HIGH PERFORMANCE APPLICATIONS

COMBO, A Step-up For More Flexibility And Agility

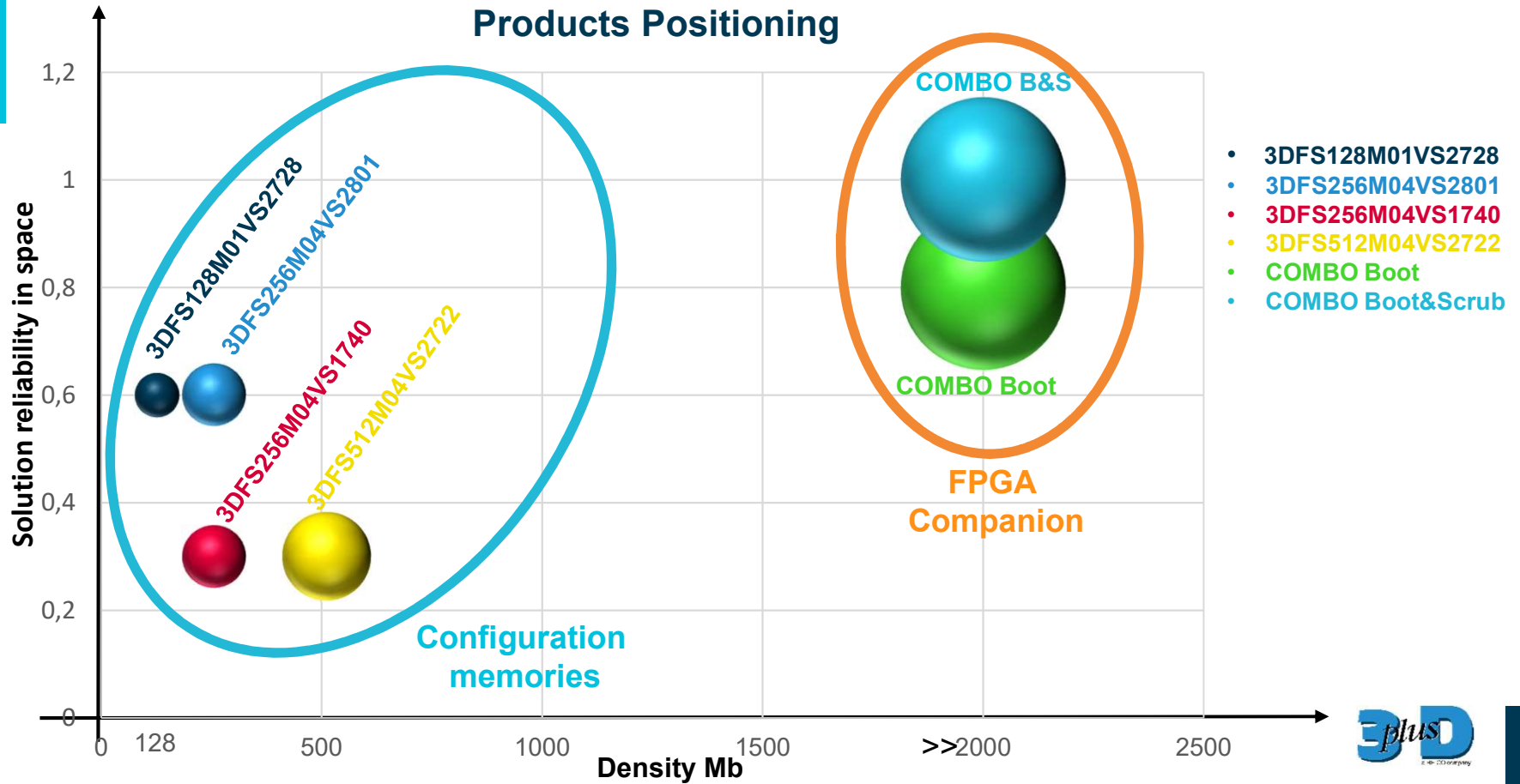
3D PLUS offers a complete ecosystem for high performance applications requiring in-flight reconfiguration :

- **DDR4 memory** to buffer the new bitstream
- **DDR4 TR** to regulate the VTT of DDR4 memory
- **RIMC DDR4** to mitigate uploaded bitstream
- **COMBO** to store multiple FPGA bitstreams and to enable in-flight reconfiguration





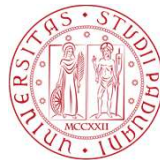
3D PLUS HD CONFIGURATION SOLUTIONS POSITIONING





MNEMOSYNE

Rad-Hard Non-Volatile Memory





MNEMOSYNE REQUIREMENT

Space Design Community Need



Higher density ROMs required:

- Users applications
- FPGAs/MPSOCs:
 - ZynQ UltraScale + (ZCZU15): ≥ 512 Mb
 - Versal -XQRV : ≥ 1 Gb

AMD XILINX Space FPGAs	Configuration memory density
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Conf. Memory preserves data integrity from start till end of mission

- Data retention
- Non volatile
- SEL immunity
- SEU immunity





MNEMOSYNE INTRODUCTION

The Memory Goddess



- ◆ **Non volatile memory with SPI interface**
- ◆ **High Density**
- ◆ **Radiation Immune**
- ◆ **Developped by 3D PLUS** in the frame of a EU Horizon 2020 research and innovation program
- ◆ **Guaranteed supply chain - fully manufactured in Europe**
- ◆ **Users' Cross validated** by a consortium of Radiation Effects and Space Electronics experts:
- ◆ **Applications:**
 - ◆ FPGA configuration bitstream storage
 - ◆ Boot code storage for microcontrollers and microprocessors



MNEMOSYNE INTRODUCTION

The Project Baseline/Key Trade-offs



- ◆ **STT-MRAM** has the best performances among NVM process:
 - ◆ **Memory cell is SEU immune**
- ◆ **Rad Hard design techniques** on analog and power blocks, control logic and interfaces
- ◆ **22 nm FDSOI Technology**
 - ◆ **SEL immune chip**
 - ◆ Existing **Rad Hard Digital library** (DFF, Logic gates, ...)
 - ◆ **Mature, reliability proven** and commercially available in Europe process
 - ◆ Providing up to **40% die scaling, and nearly 70% power saving vs 28 nm**
 - ◆ **Could reach the 128 Mbit density on ASIC with small chip size**
- ◆ **High Added value functions** implemented for health monitoring and telemetry of the chip
- ◆ **3D PLUS Space Qualified packaging**
 - ◆ Achieve higher memory densities with stacking of multiple 128 Mb chips
- ◆ Large Users consortium for **extensive « designer/manufacture independent » validation and qualification tests**



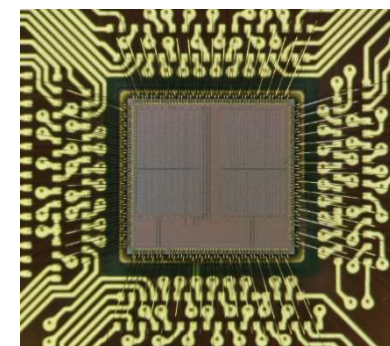
MNEMOSYNE FIRST DESIGN

The First Silicon and Test Vehicle Design



ASIC RHBD techniques summary

- Memory cell is SEU immune (STT-MRAM) and SEL immune (FD-SOI process)
- Small technology node i.e. very thin gate oxide, no significant variation in MOS threshold.
- Body-bias techniques to reduce leakage
- Rad hard design techniques on control logic and interfaces
- TMR
- SET immune cells on clock and reset trees
- Glitch filters on strategic nodes
- Derating accounting for device aging and TID.



ASIC Test vehicle



Module Test vehicle

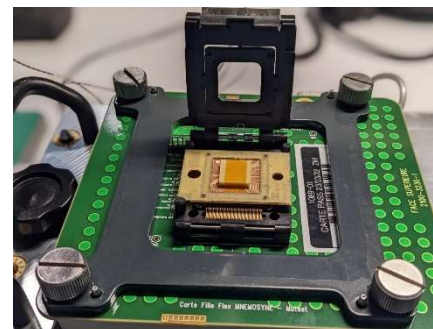
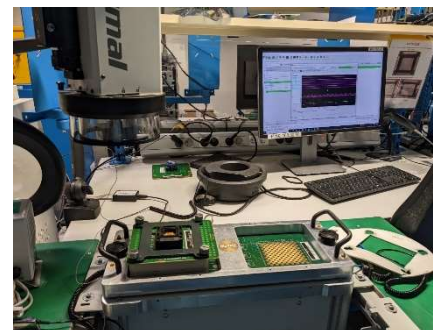


FIRST DESIGN RESULTS

Results Summary



- ❏ TID > 100 krad(Si)
- ❏ SEL/SEU LET_h > 60 MeV.cm²/mg
- ❏ 1000h Life test passed with 3 θ measurements
- ❏ Overall Functional and Performance validated
- ❏ Go for the 128 Mb Chip

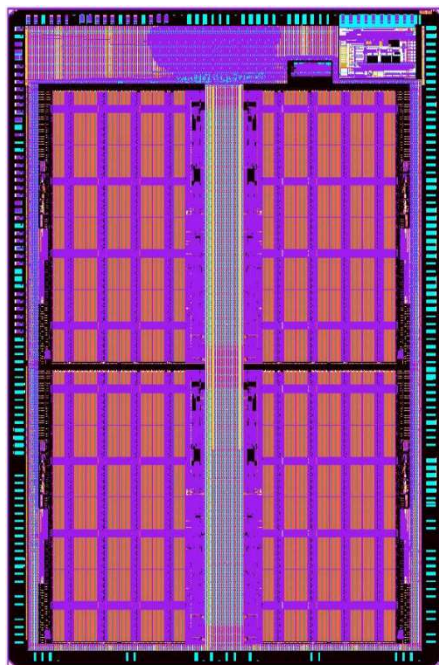


MNEMOSYNE Electrical tests

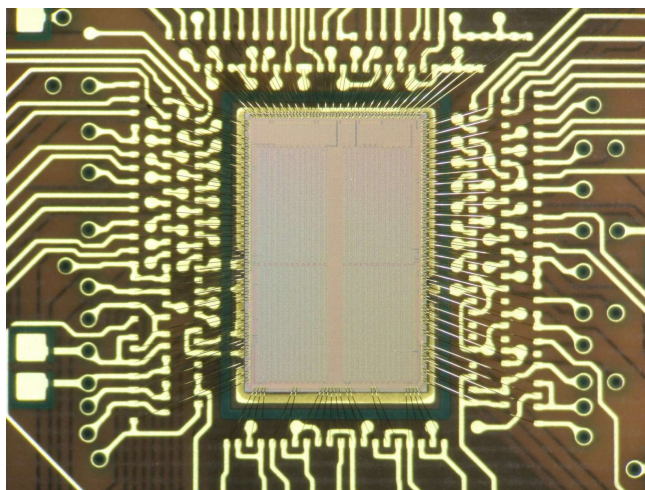


NEW DESIGN

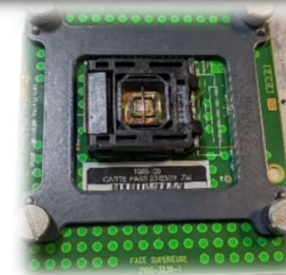
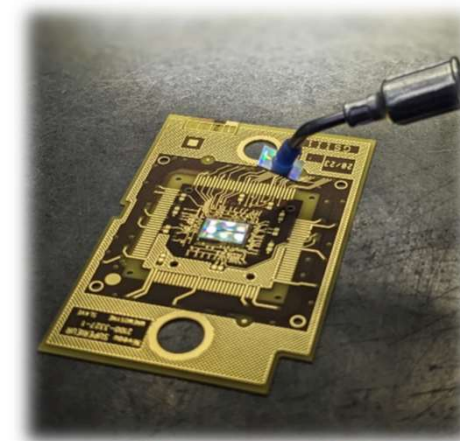
ASIC received



128 Mbit ASIC layout



128 Mbit ASIC die bonded





NEW DESIGN

First Results



TV results confirmed

- ❏ TID > 100 krad(Si)
- ❏ SEL/SEU LET_h > 60 MeV.cm²/mg
- ❏ 1000h Life test passed with 3 θ measurements
- ❏ Overall Functional and Performance validated
- ❏ Magnetic tests on-going





MNEMOSYNE CHARACTERISTICS

High Density Radiation Hardened NVM



KEY FEATURES

- ◆ 512 Mb, 1 Gb density
- ◆ Up to 100 MHz
- ◆ 1.8 V SPI interface (3.3 V optional)
- ◆ SPI, QSPI, OSPI supported
- ◆ Embedded ECC
 - ECC flag
 - Error counter
- ◆ 100 k P/E cycles
- ◆ 20 years data retention
- ◆ [-55 °C; +125 °C]: op. temp

RADIATION DATA

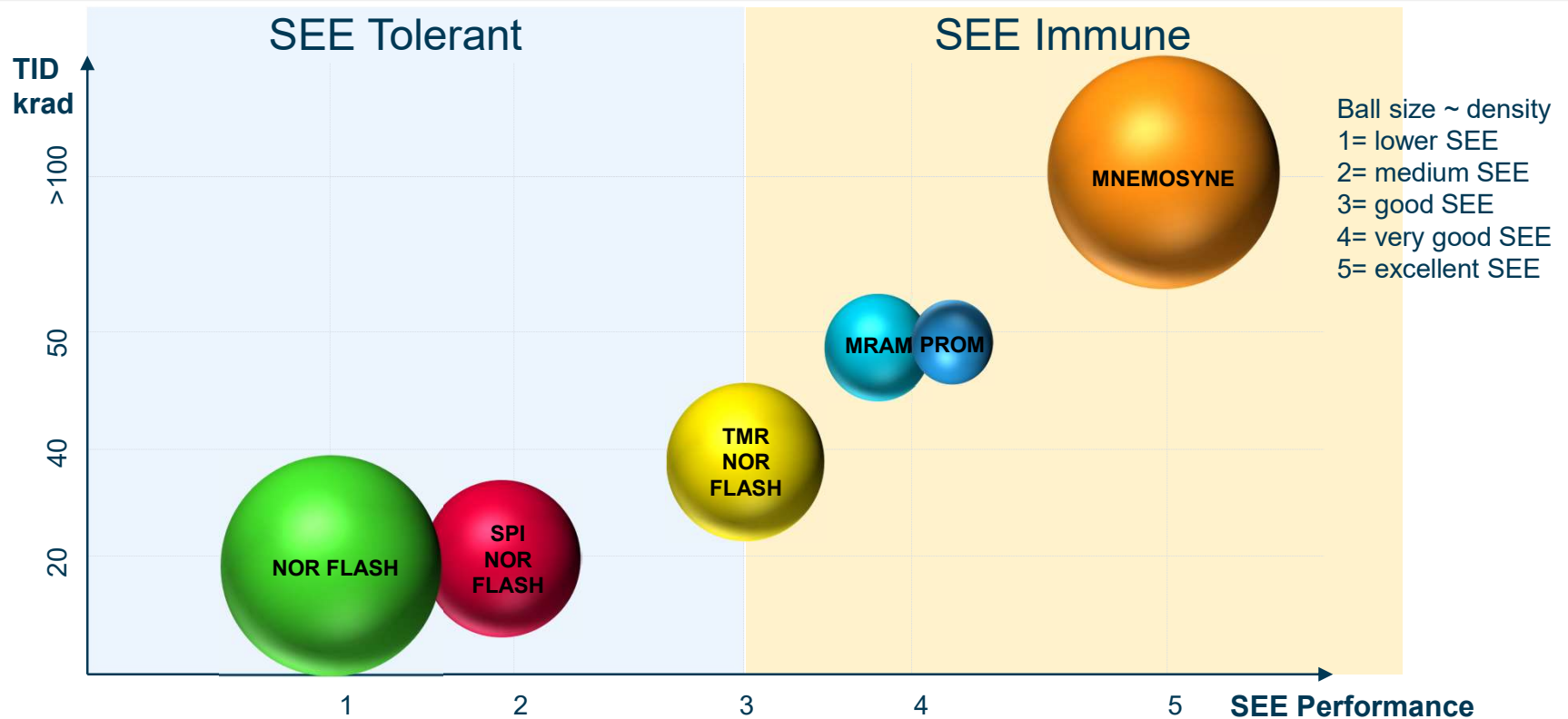
- ◆ TID > 100 krad(Si)
- ◆ SEL > 60 MeV.cm²/mg
- ◆ SEU > 60 MeV.cm²/mg
- ◆ SET > 60 MeV.cm²/mg
- ◆ SEFI > 60 MeV.cm²/mg

Note: The SEE LET threshold would be tested in other facilities with 80 MeV.cm²/mg target



3D PLUS CONFIGURATION MEMORIES

Portfolio





CONCLUSION

3D PLUS Available Solutions for the last Generation of FPGAs

3D PLUS offers 2 Space grade solutions to boot high-end SRAM based FPGAs

1. COMBO

- ◆ **First delivery : October 2023**
- ◆ Full space grade solution to boot different high end SRAM based FPGAs
- ◆ System reliability increased thanks to implemented mechanisms
- ◆ Multiple reliable bitstream images with data integrity
- ◆ Key solution for on-orbit reconfiguration
- ◆ Storage of data during the mission
- ◆ Time and money savings

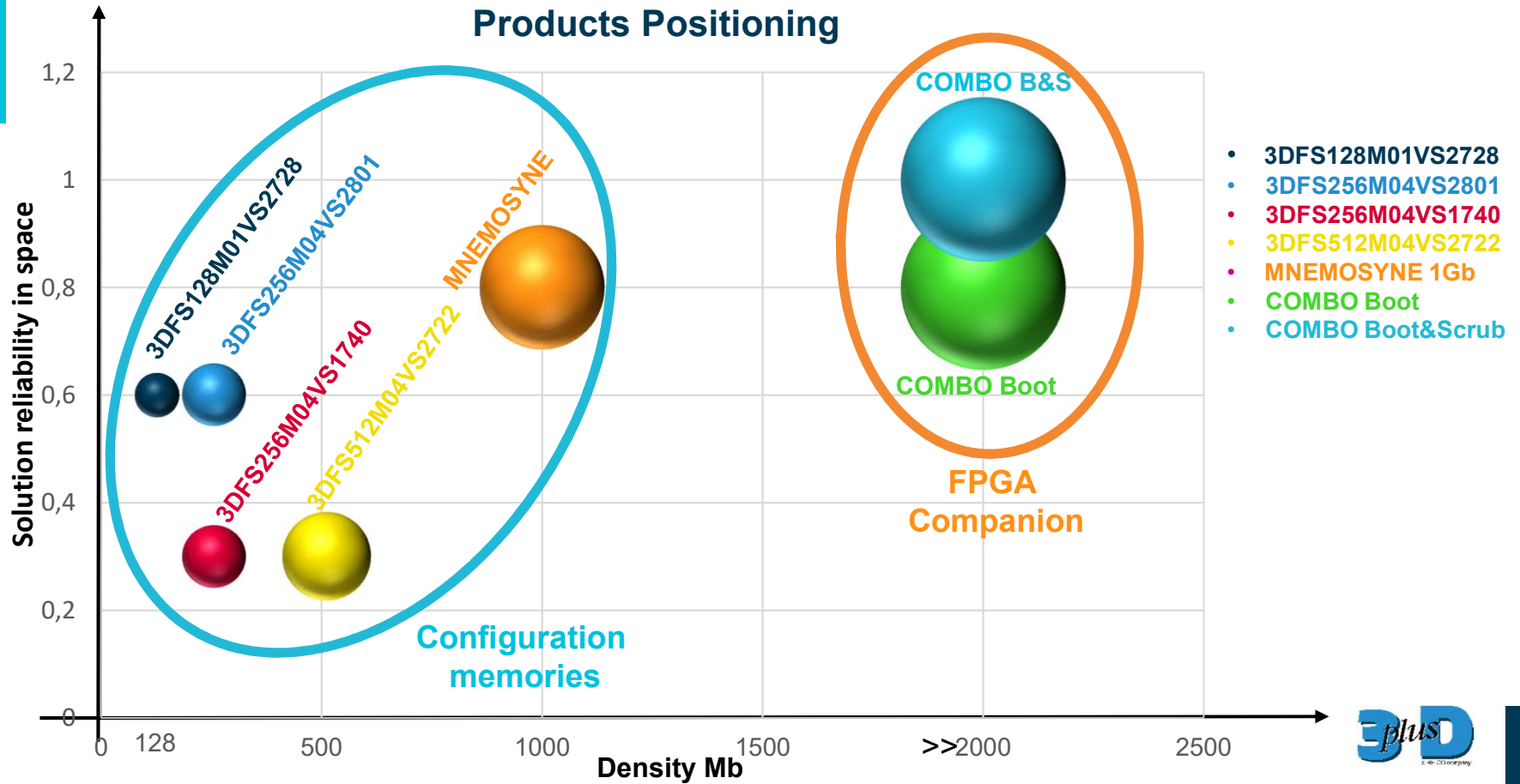
2. MNEMOSYNE

- ◆ **First delivery : September 2023**
- ◆ Space grade high density configuration memory
- ◆ Best in class regarding reliability (data retention, P/E cycles, radiation)
- ◆ Ease customers life with additional features for error management strategy (ECC_flags, errors counters)
- ◆ Scalability (512 Mbit & 1 Gbit are pin to pin compatible)





3D PLUS HD CONFIGURATION SOLUTIONS POSITIONING



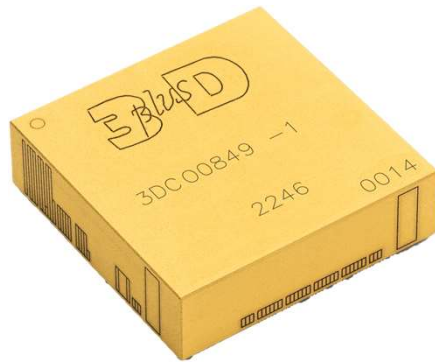


AKNOWLEDGEMENTS

High Density Radiation hardened NVM (MNEMOSYNE)



- ◆ The authors and partners' co-authors (IMEC: Paul Zuber, Geert Thys; University Padova: Simone Gerardin, Marta Bagatin; TRAD: Lionel Gouyet) would like to thank the European Commission and all the members of the consortium that are driving this project.
- ◆ The MNEMOSYNE project is funded by EU Horizon 2020 research and innovation program under grant agreement 870415 (call: H2020 - SPACE-2019).
- ◆ MNEMOSYNE, together with EFESOS which is another H2020 project led by IMEC focused on RH DARE22 platform (GA 821883), is also developing the 22nm FDSOI RH design



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